2N6667, 2N6668

Designed for general−purpose amplifier and low speed switching applications.

- High DC Current Gain −
  h_{FE} = 3500 (Typ) @ I_C = 4.0 Adc
- Collector−Emitter Sustaining Voltage − @ 200 mAdc
  $V_{CEO(sus)}$ = 60 Vdc (Min) − 2N6667
  = 80 Vdc (Min) − 2N6668
- Low Collector−Emitter Saturation Voltage −
  $V_{CE(sat)}$ = 2.0 Vdc (Max)@ I_C = 5.0 Adc
- Monolithic Construction with Built−In Base−Emitter Shunt Resistors
- TO−220AB Compact Package
- Complementary to 2N6387, 2N6388
- These Devices are Pb−Free and are RoHS Compliant*

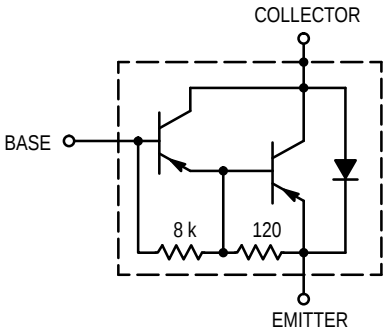
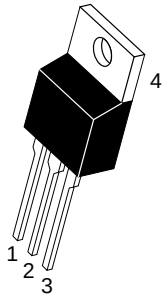


Figure 1. Darlington Schematic

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

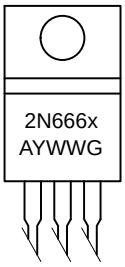
www.onsemi.com

PNP SILICON DARLINGTON POWER TRANSISTORS 10 A, 60−80 V, 65 W



TO−220
CASE 221A
STYLE 1

MARKING DIAGRAM



x = 7 or 8
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
2N6667G	TO−220 (Pb−Free)	50 Units/Rail
2N6668G	TO−220 (Pb−Free)	50 Units/Rail

Symbol	2N6667	2N6668	Unit
V_{CEO}	60	80	Vdc
V_{CB}	60	80	Vdc
V_{EB}	5.0		Vdc
I_C	10 15		Adc
I_B	250		mAdc

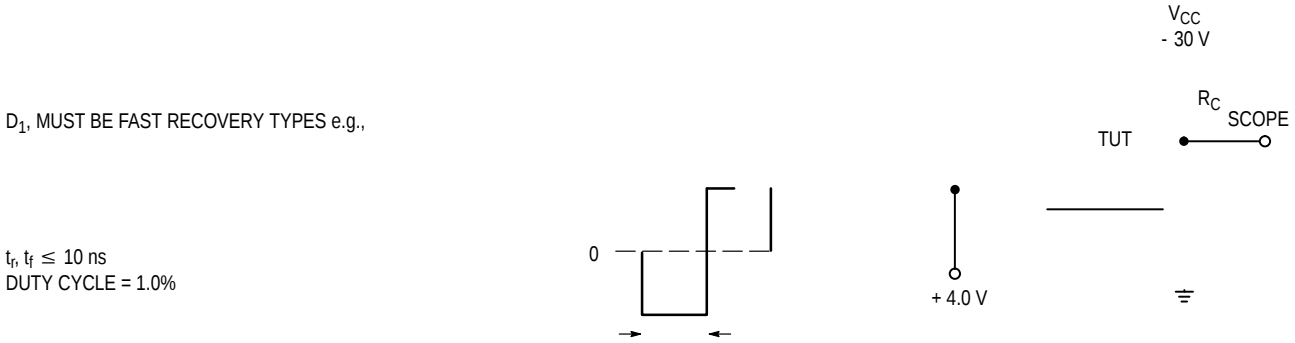


Figure 2. Switching Times Test Circuit

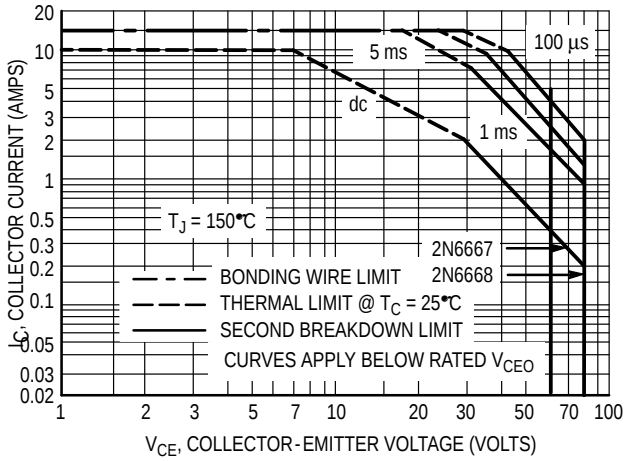


Figure 6. Maximum Safe Operating Area

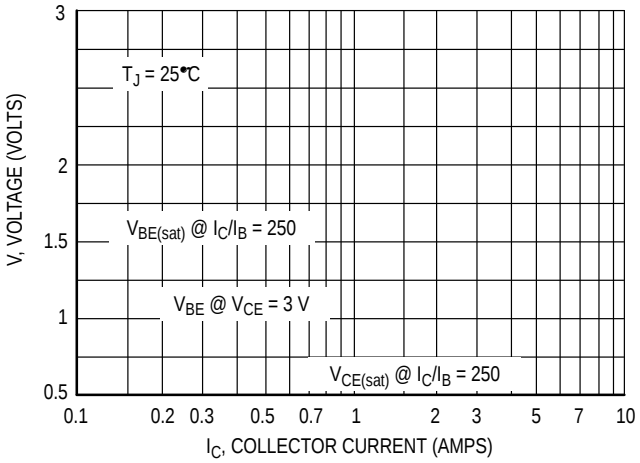


Figure 11. Typical “On” Voltages

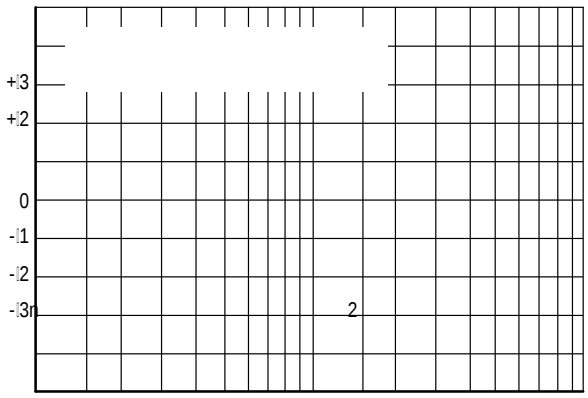


Figure 12. Typical Temperature Coefficients